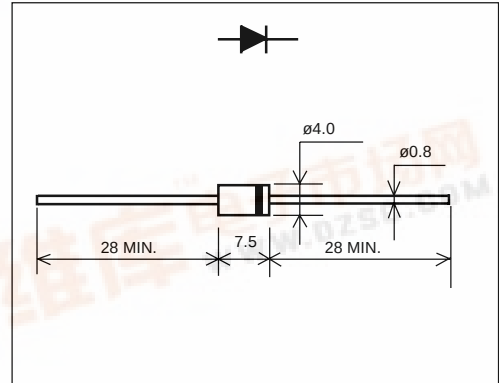


ERB32 (1.2A)

(100 to 200V / 1.2A)

FAST RECOVERY DIODE

■ Outline drawings, mm



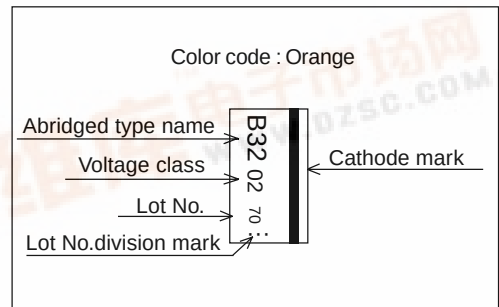
■ Features

- Super high speed switching
- Low V_F in turn on
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating		Unit
			-01	-02	
Repetitive peak reverse voltage	V_{RRM}		100	200	V
Non-repetitive peak reverse voltage	V_{RSM}		100	200	V
Average forward current	$I_{F(AV)}$	Resistive load ($T_a = 40^\circ\text{C}$)	1.2		A
Surge current	I_{FSM}	Sine wave 10ms	50		A
Operating junction temperature	T_j		-40 to +150		$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to +150		$^\circ\text{C}$

- Electrical characteristics ($T_a = 25^\circ\text{C}$ Unless otherwise specified)

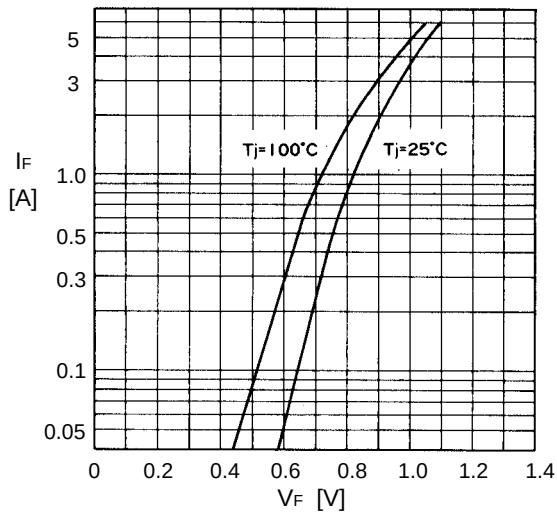
Item	Symbol	Conditions	Max.		Unit
			-01	-02	
Forward voltage drop	V_{FM}	$I_{FM} = 1.2\text{A}$	0.92		V
Reverse current	I_{RRM}	$V_R = V_{RRM}$	10	50	μA
Reverse recovery time	t_{rr}	$I_F = 0.1\text{A}, I_R = 0.1\text{A}$	100		ns

(100V to 200V / 1.2A)

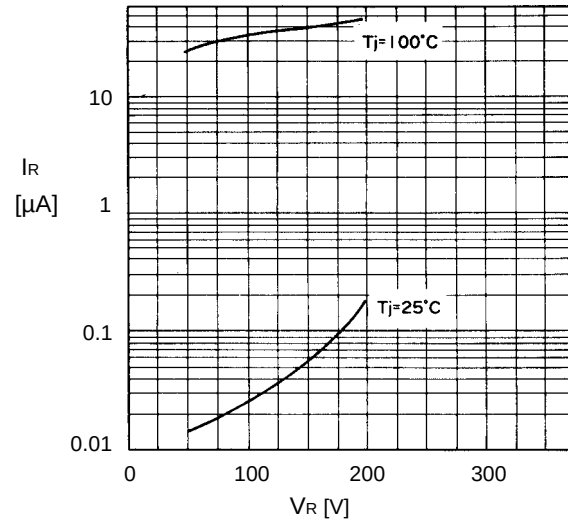
ERB32(1.2A)

■ Characteristics

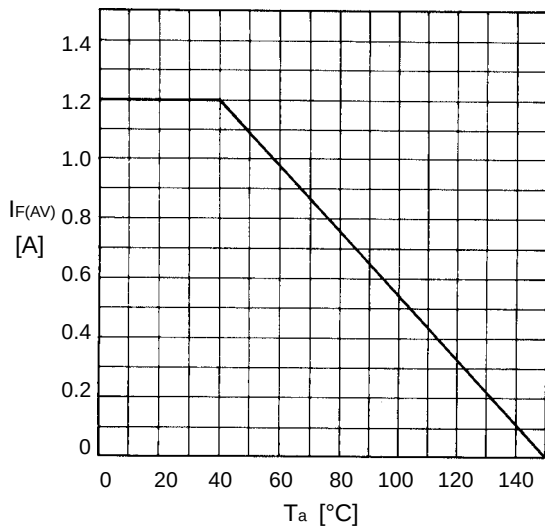
Forward characteristics



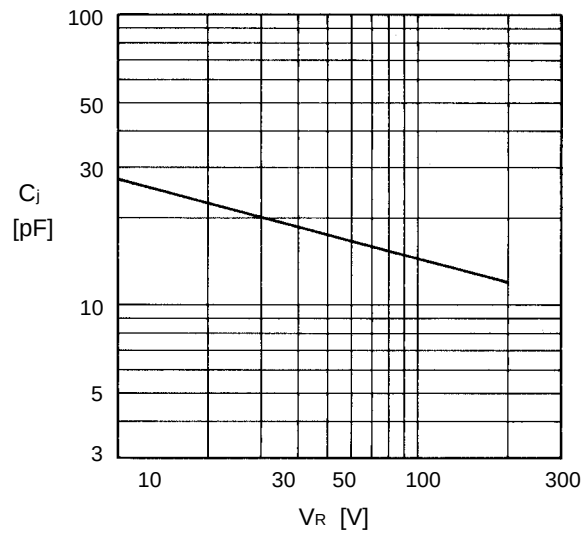
Reverse characteristics



Current derating ($I_{F(AV)}-T_a$)



Junction capacitance characteristics



Surge capability

